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Sheet 1 of 1

FORM PTO-1449 (Rev. 2-32)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	SERIAL NO. <b>NOT YET ASSIGNED</b>	DOCKET NO. <b>Q54431</b>
INFORMATION DISCLOSURE STATEMENT BY APPLICANT  (Use several sheets if necessary)		APPLICANT <b>Toshiro HAYAKAWA, Toshiaki FUKUNAGA and Mitsugu WADA</b>	
		FILING DATE <b>May 20, 1999</b>	GROUP <b>2881</b>

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>h3</i>	4,567,060	01/28/86	HAYAKAWA et al	427	87	

## FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO

## OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, etc.)

<i>h2</i>		S. O'Brien et al, High power wide aperture AlGaAs-based lasers at 870nm, January 22, 1998, Vol.34, No.2, page 184 - 186
<i>h3</i>		T. Fukunaga et al, Highly Reliable Operation of High-Power In GaAsP/InGaP/AlGaAs 0.8 $\mu$ m Separate Confinement Heterostructure Lasers, September 15, 1995, Vol. 34, No.9B, p.L1175 -L117
<i>h3</i>		J.K. Wade et al, 6.1 W continuous wave front-facet power from Al-free active-region ( $\lambda$ = 805 nm) diode lasers, January 5, 1998, Vol., 72, No.1, p.4 - 6
<i>h3</i>		M.A. Emanuel et al, High-Power Laser Diodes at Various Wavelengths, 1997, Vol. 3001, p.2 - 6
<i>h3</i>		Low-threshold room-temperature cw operation of (AlGaAs) <sub>m</sub> (GaAs) <sub>n</sub> superlattice quantum well lasers emitting at ~ 680nm, September 7, 1987, Vol.51, p.707 - 709

EXAMINER <i>JEFFER ZAHN</i>	DATE CONSIDERED <i>2/7/2001</i>
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Form PTO-1449 (Rev. 2-32)		U.S. Department of Commerce Patent & Trademark Office		Atty. Docket No. Q54431		Serial No. 09/315,068									
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				Applicant: Toshiro HAYAKAWA, et al.											
				Filing Date: May 20, 1999		Group: 2874 2881									
U.S. PATENT DOCUMENTS															
Examiner Initial		Document Number	Date	Name	Class	Sub- Class	Filing Date (if appropriate)								
13.		4,728,628	3/1/88	Fiddymet et al.	437	225									
<div style="position: absolute; top: 0; right: 0; transform: rotate(90deg);"> RECEIVED JAN 13 2001 TO 2880 MAIL ROOM </div>															
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		Document	Date	Country	Class	Sub- class	Translation Yes/No								
13.		7-74425	3/17/95	Japan	H01S	3/18									
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)															
13.		Milind R. Gokhale, et al.; "High-Power High-Efficiency 0.98-μm Wavelength InGaAs-(In)GaAs(P)-InGaP Broadened Waveguide Lasers Grown by Gas-Source Molecular Beam Epitaxy" vol. 33; No. 12; December 1997; pages 2266-2276													
13.		Electronics Letters; vol. 28; No. 16; pages 1531-1532; July 1992													
EXAMINER: JEFFREY RATH				DATE CONSIDERED: 2/7/2001											
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